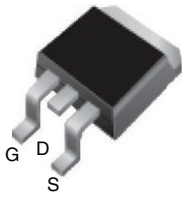
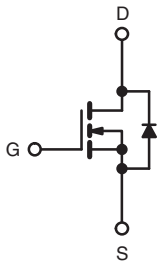
N-Channel 600-V (D-S) Super Junction MOSFET

PRODUCT SUMMARY		
V_{DS} at T_J max. (V)	600	
$R_{DS(on)}$ max. at 25 °C (Ω)	V_{GS} = 10 V	0.190
Q_g max. (nC)	98	
Q_{gs} (nC)	17	
Q_{gd} (nC)	25	
Configuration	Single	

D²PAK (TO-263)





N-Channel MOSFET

FEATURES

- Generation one
- High E_{AR} capability
- Lower figure-of-merit R_{on} x Q_g
- 100 % avalanche tested
- Ultra low R_{on}
- dV/dt ruggedness
- Ultra low gate charge (Q_g)

RoHS COMPLIANT

APPLICATIONS

- PFC power supply stages
- Hard switching topologies
- Solar inverters
- UPS
- Motor control
- Lighting
- Server telecom

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	20	A
		T_C = 100 °C		13	
Pulsed Drain Current [a]			I_{DM}	65	
Linear Derating Factor		D²PAK (TO-263)		2	W/°C
Single Pulse Avalanche Energy [b]			E_{AS}	690	mJ
Repetitive Avalanche Energy [a]			E_{AR}	25	
Maximum Power Dissipation		D²PAK (TO-263)	P_D	250	W
Drain-Source Voltage Slope	T_J = 125 °C		dV/dt	37	V/ns
Reverse Diode dV/dt [d]				5.3	
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) [c]	for 10 s			300	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 7 A.
c. 1.6 mm from case.
d. $I_{SD} \leq I_D$, dI/dt = 100 A/µs, starting T_J = 25 °C.

THERMAL RESISTANCE RATINGS					
PARAMETER		**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	D^2PAK (TO-263)	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	D^2PAK (TO-263)	R_{thJC}	-	0.5	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 1 mA		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
		V_{GS} = ± 30 V		-	-	± 1	µA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V		-	-	1	µA
		V_{DS} = 600 V, V_{GS} = 0 V, T_J = 150 °C		-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 11 A	-	0.190	-	Ω
Forward Transconductance [a]	g_{fs}	V_{DS} = 50 V, I_D = 13 A		-	9.4	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz		-	2810	-	pF
Output Capacitance	C_{oss}			-	1480	-	
Reverse Transfer Capacitance	C_{rss}			-	33	-	
Effective Output Capacitance (Time Related)	$C_{oss\ eff.}$ (TR)[a]	V_{GS} = 0 V	V_{DS} = 0 V to 480 V	-	155	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 22 A, V_{DS} = 480 V	-	75	110	nC
Gate-Source Charge	Q_{gs}			-	17	-	
Gate-Drain Charge	Q_{gd}			-	25	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 380 V, I_D = 22 A, R_g = 9.1 Ω, V_{GS} = 10 V		-	24	50	ns
Rise Time	t_r			-	68	100	
Turn-Off Delay Time	$t_{d(off)}$			-	77	115	
Fall Time	t_f			-	59	90	
Gate Input Resistance	R_g	f = 1 MHz, open drain		-	0.65	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	22	A
Pulsed Diode Forward Current	I_{SM}			-	-	88	
Diode Forward Voltage	V_{SD}	T_J = 25 °C, I_S = 22 A, V_{GS} = 0 V		-	-	1.2	V
Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = I_S, dI/dt = 100 A/µs, V_R = 25 V		-	462	690	ns
Reverse Recovery Charge	Q_{rr}			-	8.3	16	µC
Reverse Recovery Current	I_{RRM}			-	30	60	A

Note

a. $C_{oss\ eff.}$ (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

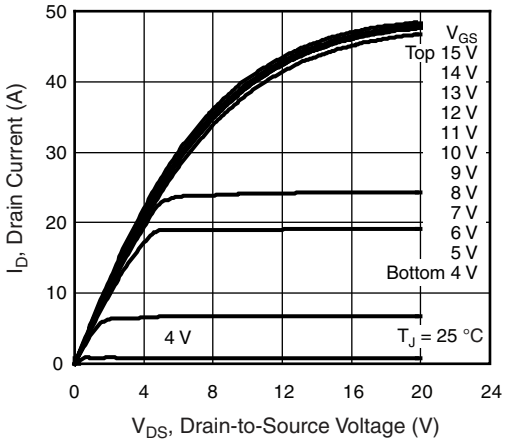


Fig. 1 - Typical Output Characteristics, T_J = 25 °C

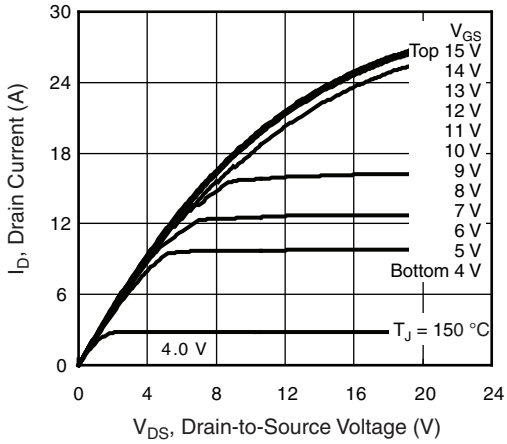


Fig. 2 - Typical Output Characteristics, T_J = 150 °C

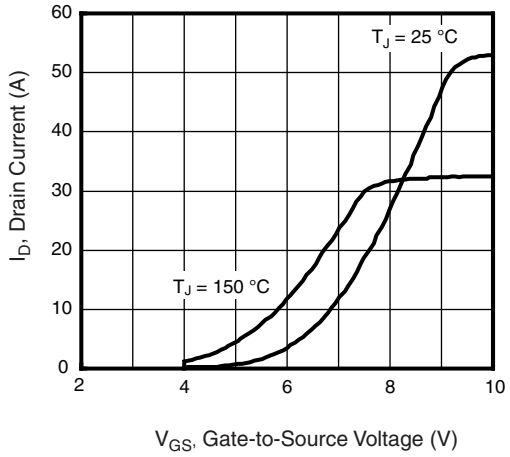


Fig. 3 - Typical Transfer Characteristics

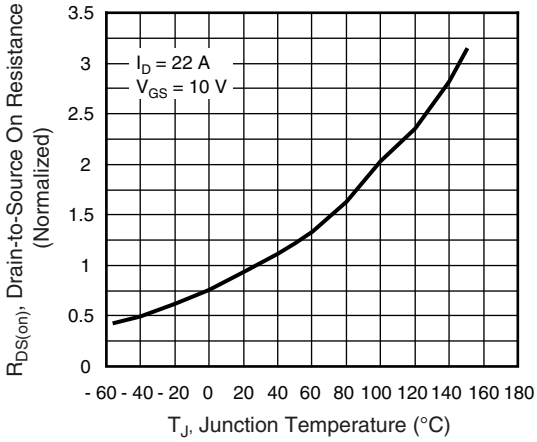


Fig. 4 - Normalized On-Resistance vs. Temperature

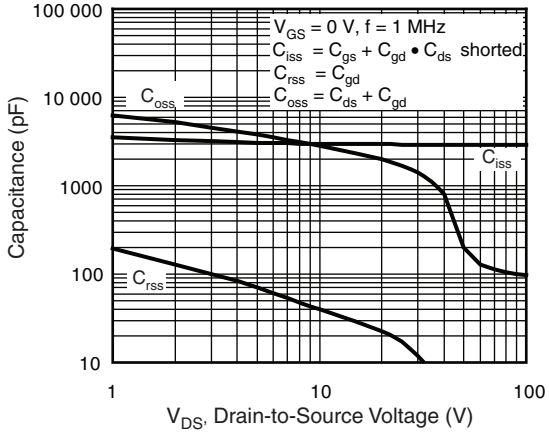


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

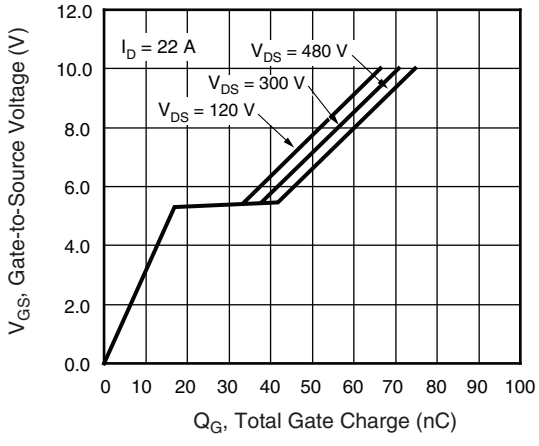


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

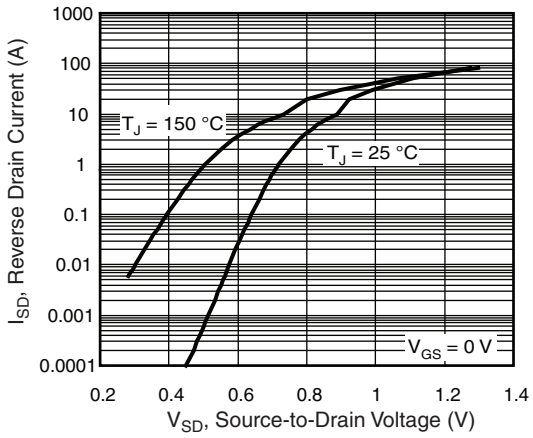


Fig. 7 - Typical Source-Drain Diode Forward Voltage

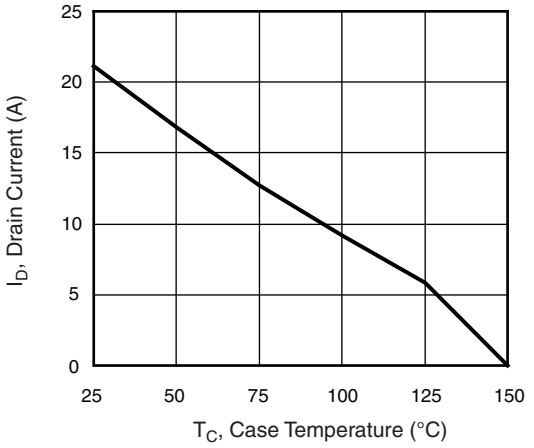


Fig. 9 - Maximum Drain Current vs. Case Temperature

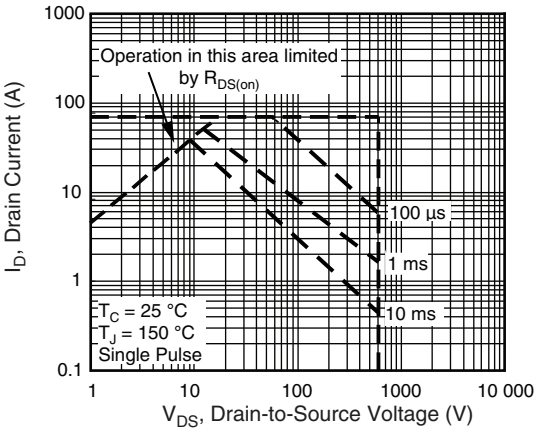


Fig. 8 - Maximum Safe Operating Area

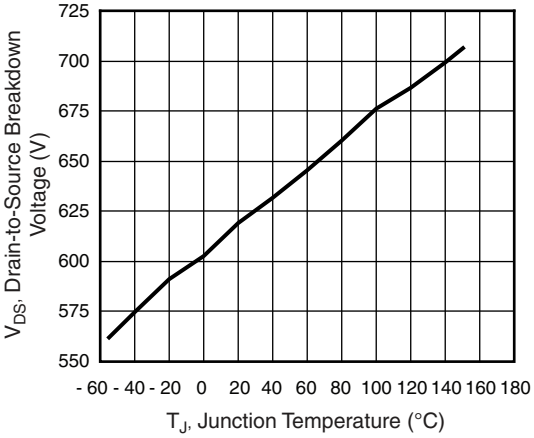


Fig. 10 - Drain-to-Source Breakdown Voltage

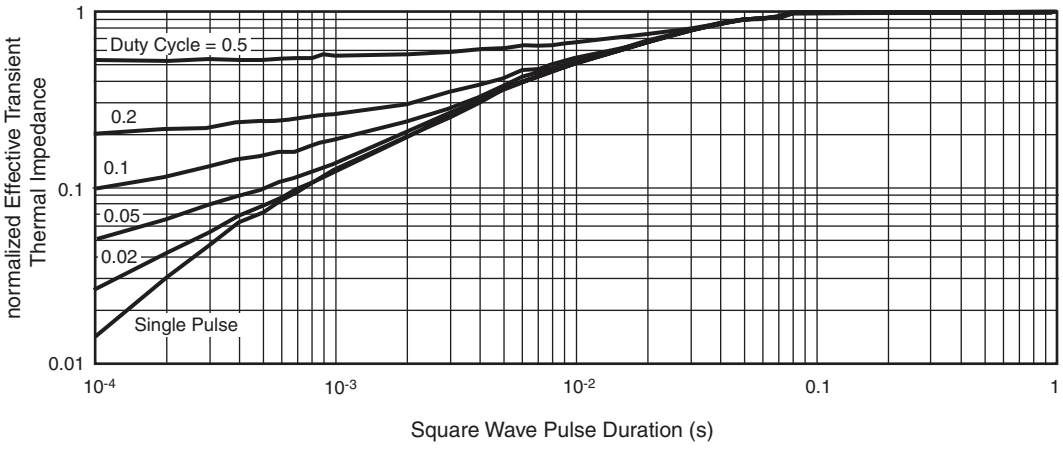


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

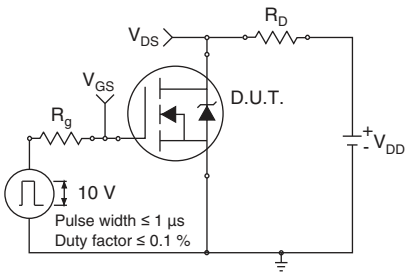


Fig. 12 - Switching Time Test Circuit

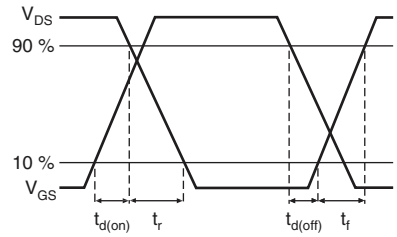


Fig. 13 - Switching Time Waveforms

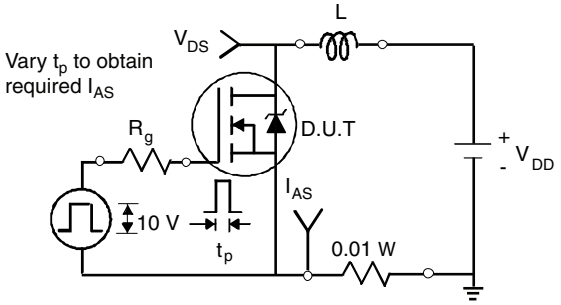


Fig. 14 - Unclamped Inductive Test Circuit

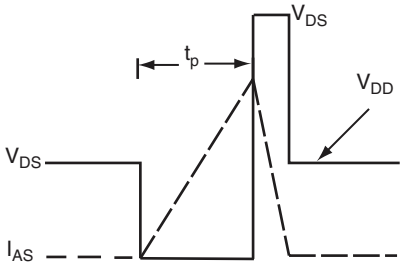


Fig. 15 - Unclamped Inductive Waveforms

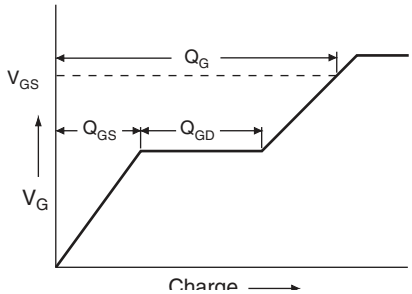


Fig. 16 - Basic Gate Charge Waveform

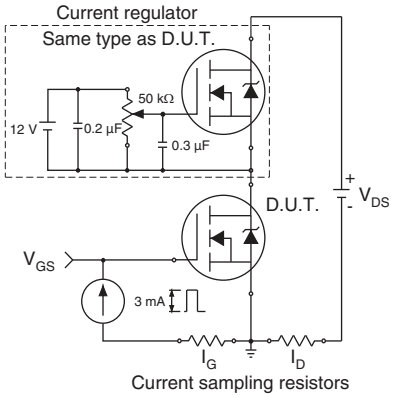
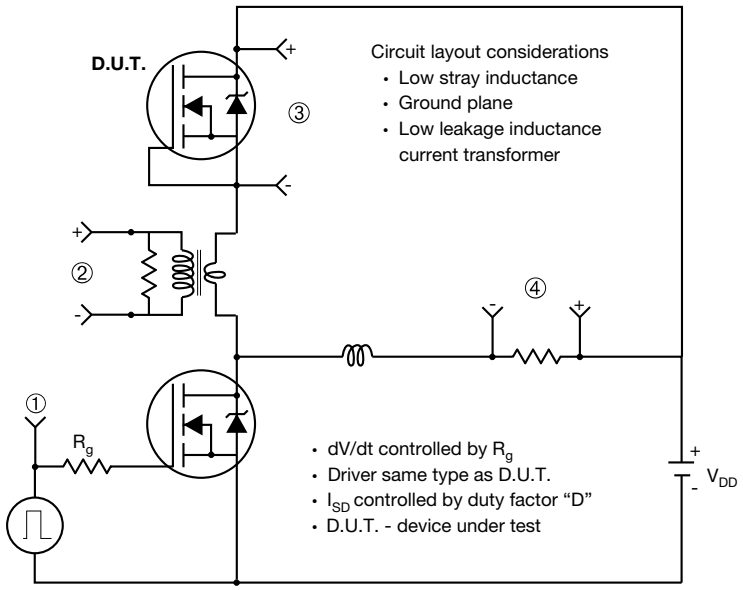
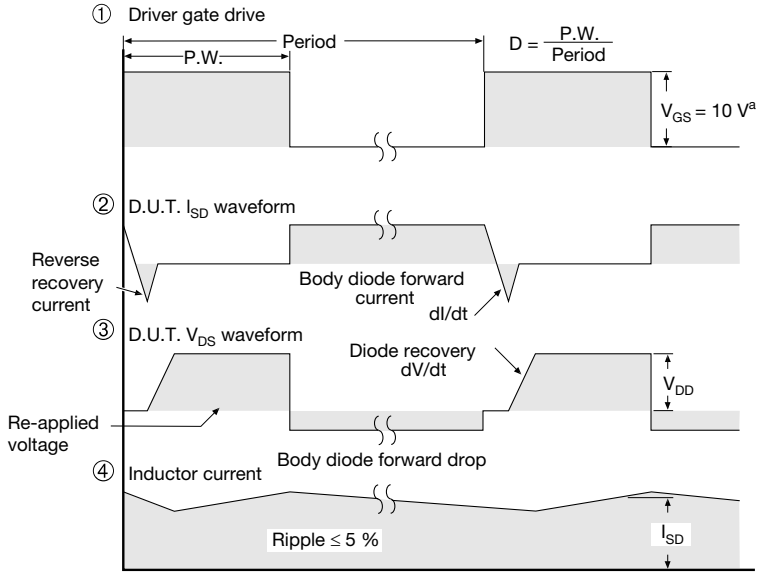


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



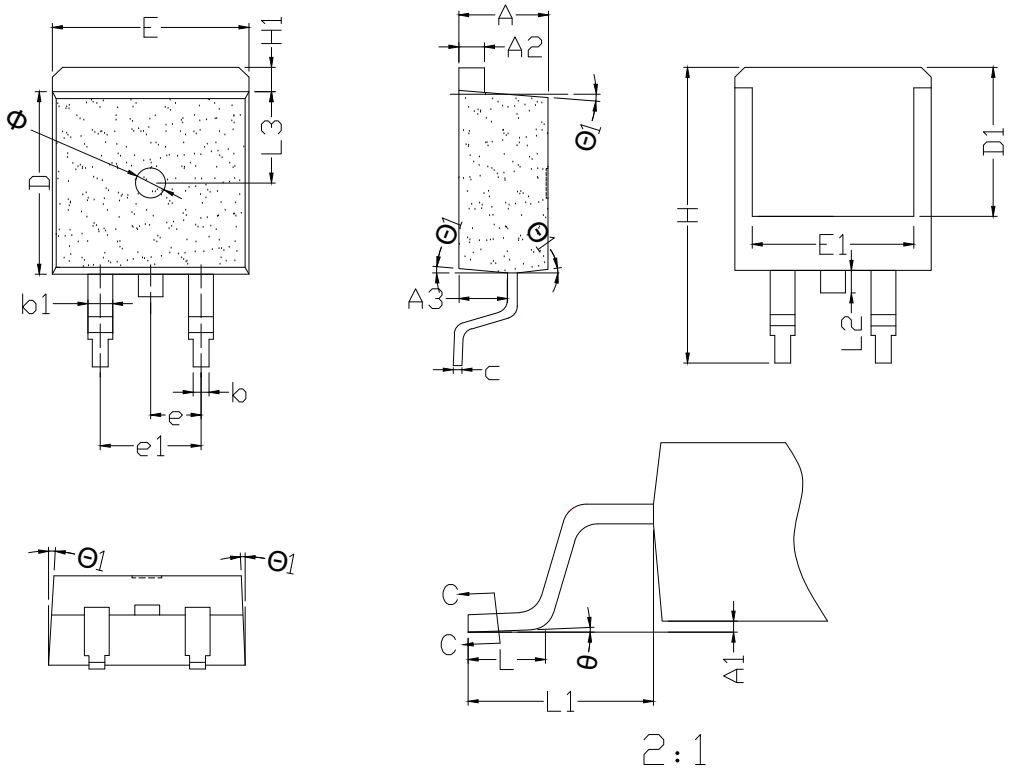


Note

a. V_{GS} = 5 V for logic level devices

Fig. 18 - For N-Channel

TO-263 PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.10	4.50	4.80	e	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	H	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
c	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1	7.50REF			ϕ	0°	2°	5°
E	9.60	10.02	10.80	ϕ1	2°	-	7°
E1	7.60	9.88	10.30	Φ	1.5BSC		

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